SHEET 1 OF 1

<b>**</b>					POCKETNO	CERI	AL NO.			
TRANSFORMATION DISCLOSURE							15,777			
CITATION IN AN					6/101-039					
APPLICATION						l				
	Ar	'PL	CATION		ADDITIONAL					
					APPLICANT Hideto HIDAKA					
(PTO-1449)					FILING DATE GROUP <b>July 10, 2003 GROUP 2811</b>					
				U.S. PATENT	DOCUMENTS					
Publication Date					Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant			
EXAMINER'S INITIALS	CITE NO.	TE Number-Kind Codes (2 lonos		MM-DD-YYYY			Figures Appear			
~~	A1	us	2002/0172073 11/21/2002 HIDAKA			Not considered				
		US.	10/327,888	12/26/2002	HIDAKA	HIDAKA		ap 11/26/2004		
		US					1 1/20/201			
		US					<del>                                     </del>			
		us			<del>  \                                   </del>					
		US			<del>                                     </del>					
	<b></b>	US								
	<u> </u>	US								
	<b>├</b> ──	US					<u> </u>			
	<del> </del>	US					ļ			
	<del> </del>	us					<del> </del>			
	<del> </del>	US					<b>├</b> ──			
	1	us			POOLINE NITE					
					Name of Patentee or	Pages, Colu	nns, Lines	Tra	nslation	
EXAMINER'S INITIALS	T		oreign Patent Document untry Codes-Number + -Kind	Publication Date MYY	Applicant of Cited Document	Where Relevant Figures Appear				
	NO.	1 "	Codes (if known)					Yes	No	
		1						abstract		
QP.	+	1	JP 2002-170375	06/14/2002	HIRAL			-		
1	1			ļ	<del>  \</del>			1		
				<b></b>	-		<del></del>			
		4-		<del> </del>	-					
			OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
							the item (bo	ook, magazin	∍ <b>.</b>   `	
EXAMINER'S INITIALS INCLUDE name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, local formula, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.										
ļ		-	SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET							
ap			SCHEUERLEIN, et al. "A 10ns Read and with Notificial Visits of Circuits Conference (2000) TA 7.2  Switch in Each Cell" IEEE International Solid-State Circuits Conference (2000) TA 7.2  DURLAM, et al. "Nonvotatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits  Conference (2000) TA 7.3							
62			DURLAM, et al. "Nonvolati	ne Kawi based on IV	Conference (2000) TA 7.3			ula Contaca		
NAJI, et al. "A 256kb 3.0V 1T1MJT Nonvolatile Magnetoresistive RAM" IEEE International Solid-State Circuits Conference (2001) TA 7.6									100	
1-5										
			- Lung		11/26/20					
	Cen	<u>m</u>	1 min	otion is in conforma	nce with MPEP 609. Draw line the	rough citation	f not in con	formance and	not considere	

\*EXAMINER: Initial if reference considered, whether of dot citation is in conformance with MPEP 609. Draw line through citation if not in conformal Include copy of this form with next communication by applicant.

1 Applicant's unique citation designation number (obtional). 2 Applicant is to place a check mark here if English language Translation is attached.